



Solid State Devices, Inc.

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SED30KB45 SED30KE45

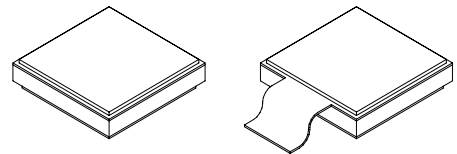
Designer's Data Sheet

FEATURES:

- Low Reverse Leakage
- Low Forward Voltage Drop
- Hermetically Sealed Surface Mount Package
- Guard Ring for Overvoltage Protection
- Eutectic Die Attach
- 175°C Operating Temperature
- TX, TXV, and Space Level Screening Available. Contact Factory.

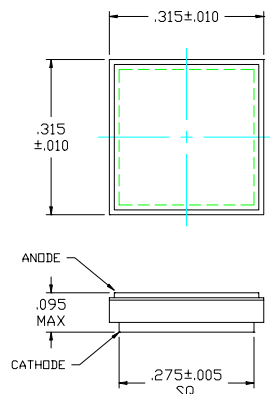
**30 AMPS
45 VOLTS
POWER SCHOTTKY DIODE**

SEDPACK 2

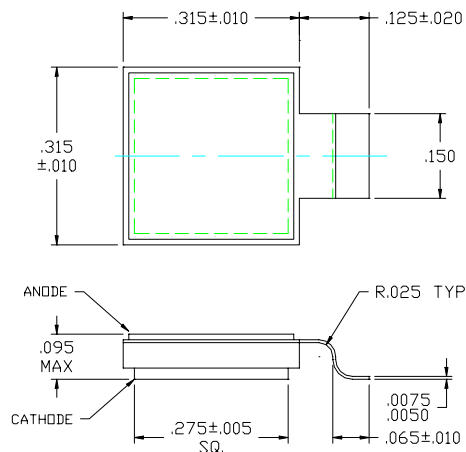


MAXIMUM RATINGS	Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_A = 100^\circ\text{C}$)	I_o	30	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, Superimposed on I_o , Allow Junction to Reach Equilibrium between Pulses, $T_A = 25^\circ\text{C}$)	I_{FSM}	500	Amps
Operating and Storage Temperature	T_{OP} & T_{stg}	-55 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	0.80	$^\circ\text{C/W}$

CASE OUTLINE: SED30KB45



CASE OUTLINE: SED30KE45



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0032A

DOC



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ELECTRICAL CHARACTERISTICS	Symbol	-55	25	100	125	150	Unit
Instantaneous Forward Voltage Drop, typical ($I_F = 5$ Amps, 300 μ sec Pulse) maximum	V_F	455 520	350 400	250 -	210 275	180 -	mVolts
Instantaneous Forward Voltage Drop, typical ($I_F = 15$ Amps, 300 μ sec Pulse) maximum	V_F	490 580	400 475	320 -	290 375	265 -	mVolts
Instantaneous Forward Voltage Drop, typical ($I_F = 30$ Amps, 300 μ sec Pulse) maximum	V_F	525 620	455 530	395 -	370 450	355 -	mVolts
Reverse Leakage Current typical (Rated V_R , 300 μ sec pulse minimum) maximum	I_R	0.015 -	0.31 5	50 -	175 300	485 -	mA
Junction Capacitance typical ($V_R = 10$ V _{DC} , $T_A = 25^\circ$ C, $f = 1$ MHz) maximum	C_J	-	2200 2600	-	-	-	pF

